NSN 5961-01-092-6580

Transistor - Page 1 of 2



view Online at https://aerobasegroup.com/nsn/5961-01-092-6560
Inclosure Material:
Metal
Overall Length:
1.573 inches
Overall Height:
0.450 inches
Overall Width:
0.875 inches
End Application:
Strategic weapon systems (poseidon and trident); nimitz class cvn; aircraft, galaxy c-5; usns stalwart class tagos; integrated underwater
surviellance systems; forrestal class cv; missile, air launch xruise (alcm) agm-86b
Mounting Facility Quantity:
2
Internal Configuration:
Junction contact
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
To-3
Electrode Internally-electrically Connected To Case:
Collector
Mounting Method:
Unthreaded hole
Features Provided:
Hermetically sealed case
Criticality Code Justification:
Feat
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
100.0 breakdown voltage, collector-to-base, emitter open and 80.0 breakdown voltage, collector-to-emitter, base open and 7.0
breakdown voltage, emitter-to-base, collector open
Current Rating Per Characteristic:
Between 7.00 amperes source cutoff current and 15.00 amperes source cutoff current
Power Rating Per Characteristic:
150.0 watts small-signal input power, common-collector
Maximum Operating Tempurature Per Measurement Point:
200.0 degrees celsius junction
Special Features:
Weapon system essential; junction pattern arrangement: npn
Terminal Type And Quantity:
1 case and 2 pin
Specification Data:
80131-release6314 professional/industrial association specification

N/a

Shelf Life:

NSN 5961-01-092-6580

Transistor - Page 2 of 2



			ure:	

--

Demilitarization:

No

Fiig:

A110a0